

NVD5C464NL

Power MOSFET

40 V, 5.2 mΩ, 64 A, Single N-Channel

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V_{DSS}	40	V	
Gate-to-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current $R_{\theta JC}$ (Notes 1 & 3)	Steady State	$T_C = 25^\circ\text{C}$	64	A
		$T_C = 100^\circ\text{C}$	45	
Power Dissipation $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	34	W
		$T_C = 100^\circ\text{C}$	19	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2 & 3)	Steady State	$T_A = 25^\circ\text{C}$	18	A
		$T_A = 100^\circ\text{C}$	12	
Power Dissipation $R_{\theta JA}$ (Notes 1 & 2)	Steady State	$T_A = 25^\circ\text{C}$	3.1	W
		$T_A = 100^\circ\text{C}$	1.5	
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	I_{DM}	340	A
Operating Junction and Storage Temperature	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$	
Source Current (Body Diode)	I_S	33	A	
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}, I_{L(pk)} = 5.2 \text{ A}$)	E_{AS}	158	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain) (Note 1)	$R_{\theta JC}$	3.76	$^\circ\text{C}/\text{W}$
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	48	

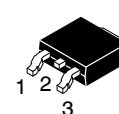
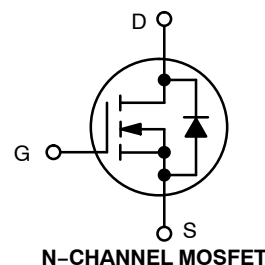
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



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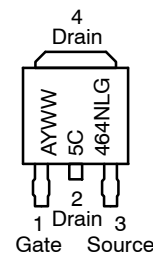
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$V_{(BR)DSS}$	$R_{DS(on)}$	I_D
40 V	5.2 mΩ @ 10 V	64 A
	7.7 mΩ @ 4.5 V	



DPAK
CASE 369C
STYLE 2

MARKING DIAGRAM & PIN ASSIGNMENT



A = Assembly Location
Y = Year
WW = Work Week
5C464NL = Device Code
G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

NVD5C464NL

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			26		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 40 V	T _J = 25°C		10	μA
			T _J = 125°C		250	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = 20 V			100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.2		2.2	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			5		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 30 A		6.4	7.7	mΩ
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A		4.3	5.2	mΩ
Forward Transconductance	g _{FS}	V _{DS} = 3 V, I _D = 30 A		74		S

CHARGES, CAPACITANCES AND GATE RESISTANCES

Input Capacitance	C _{iss}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 25 V		1600		pF
Output Capacitance	C _{oss}			600		
Reverse Transfer Capacitance	C _{rss}			34		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 32 V, I _D = 30 A		13		nC
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 32 V, I _D = 30 A		27		nC
Threshold Gate Charge	Q _{G(TH)}			2.9		
Gate-to-Source Charge	Q _{GS}			5.1		
Gate-to-Drain Charge	Q _{GD}			4.5		
Plateau Voltage	V _{GP}			3.2		

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	t _{d(on)}	V _{GS} = 10 V, V _{DS} = 32 V, I _D = 30 A, R _G = 2.5 Ω		11		ns
Rise Time	t _r			38		
Turn-Off Delay Time	t _{d(off)}			50		
Fall Time	t _f			16		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 30 A	T _J = 25°C		0.9	1.2	V
			T _J = 125°C		0.8		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 30 A		34		ns	
Charge Time	t _a			17			
Discharge Time	t _b			17			
Reverse Recovery Charge	Q _{RR}			20			nC

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

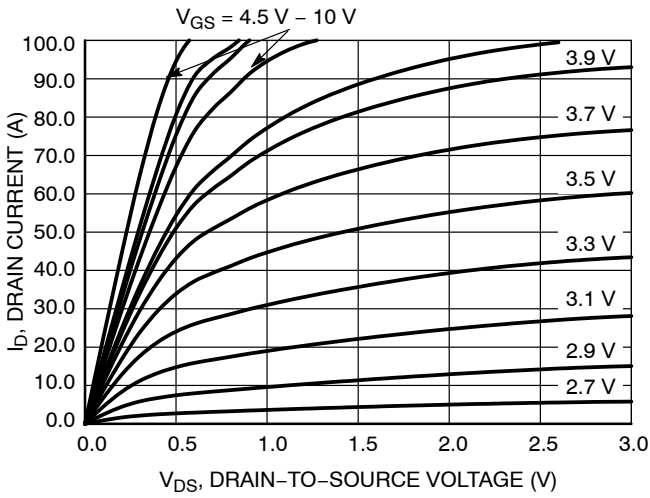


Figure 1. On-Region Characteristics

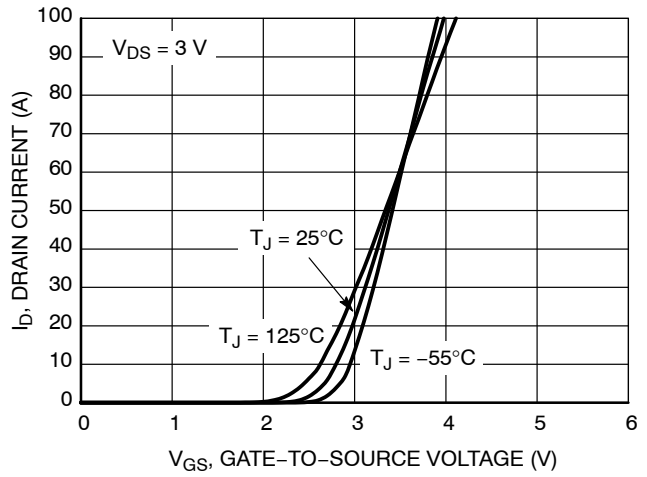


Figure 2. Transfer Characteristics

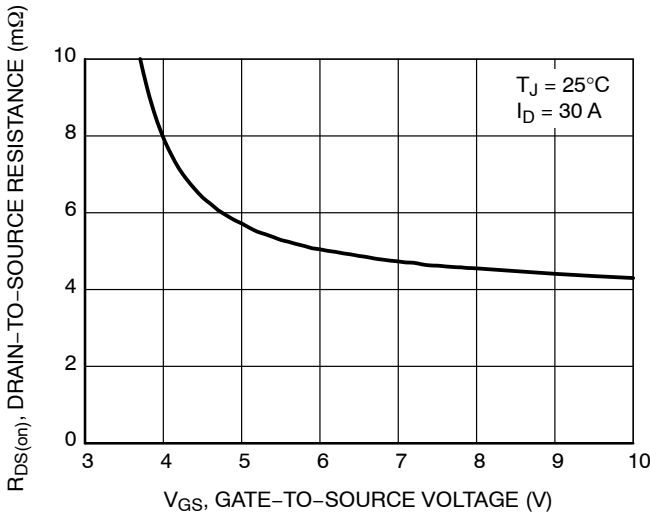


Figure 3. On-Resistance vs. Gate-to-Source Voltage

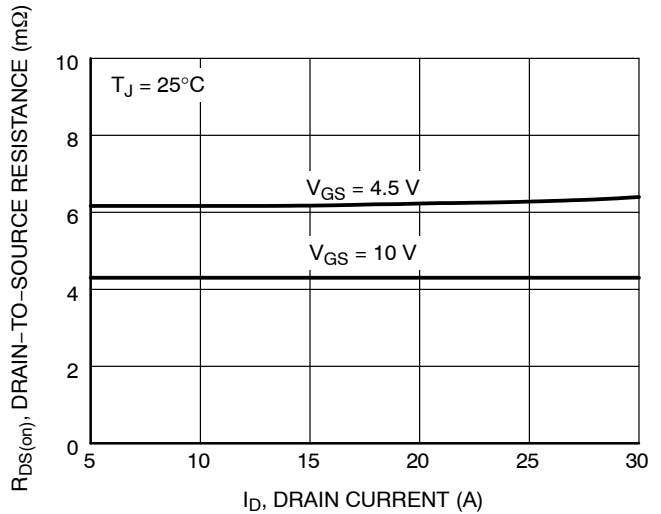


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

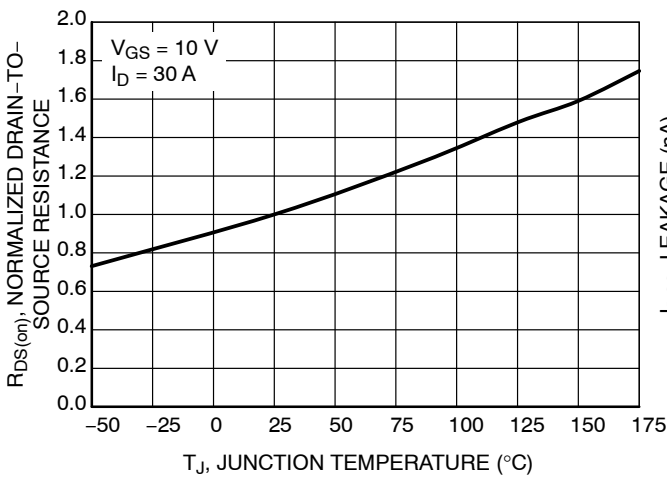


Figure 5. On-Resistance Variation with Temperature

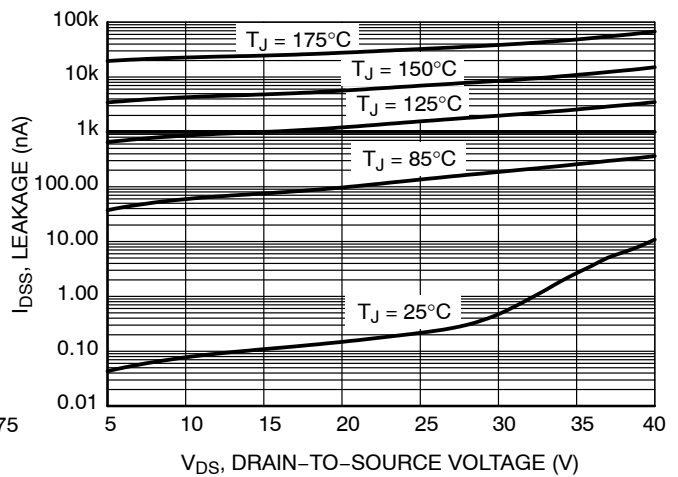


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NVD5C464NL

TYPICAL CHARACTERISTICS

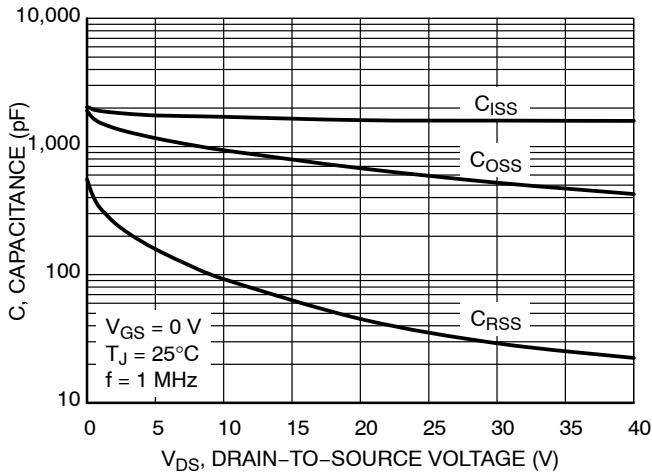


Figure 7. Capacitance Variation

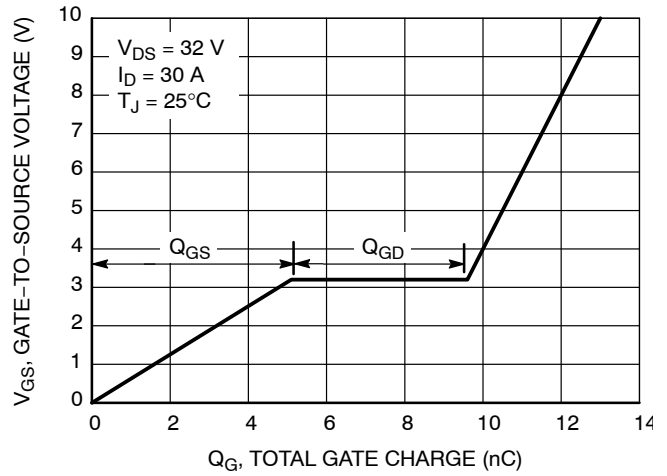


Figure 8. Gate-to-Source vs. Total Charge

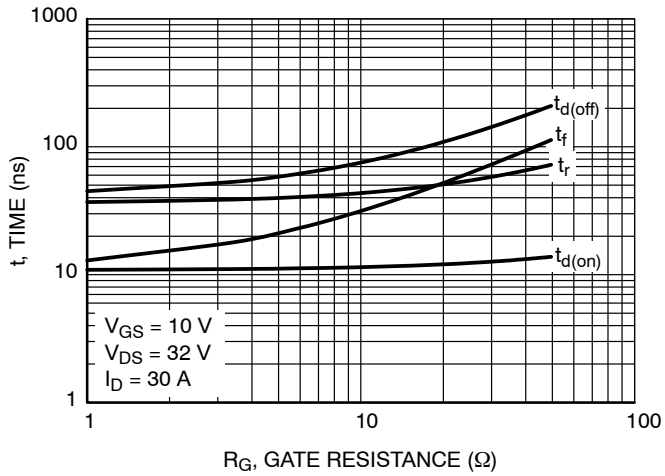


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

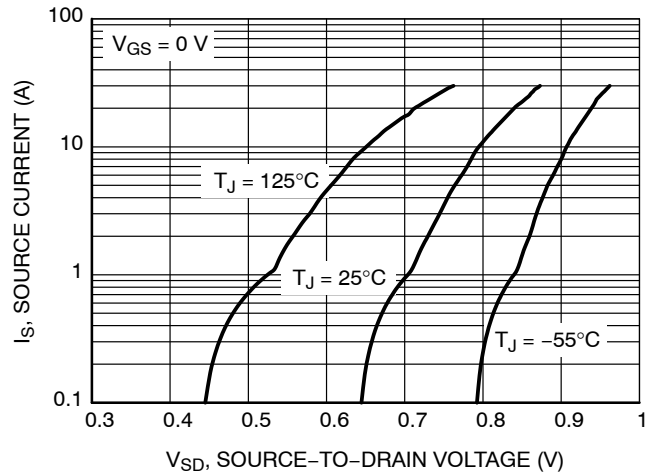


Figure 10. Diode Forward Voltage vs. Current

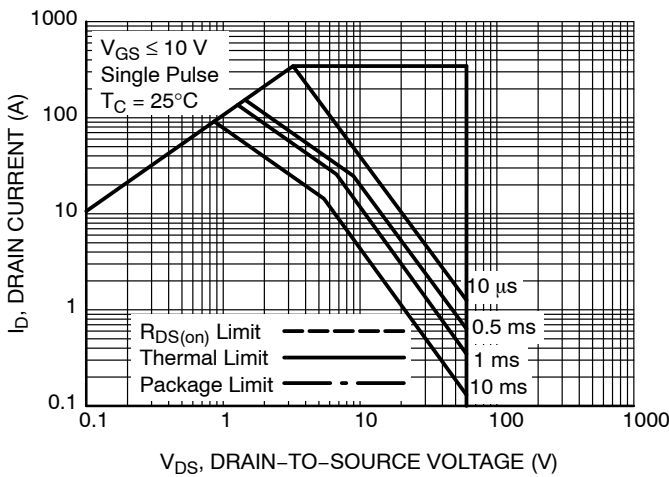


Figure 11. Maximum Rated Forward Biased Safe Operating Area

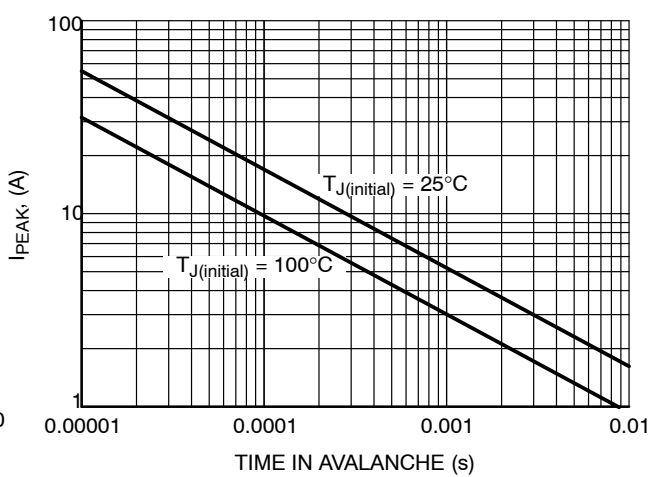


Figure 12. Maximum Drain Current vs. Time in Avalanche

NVD5C464NL

TYPICAL CHARACTERISTICS

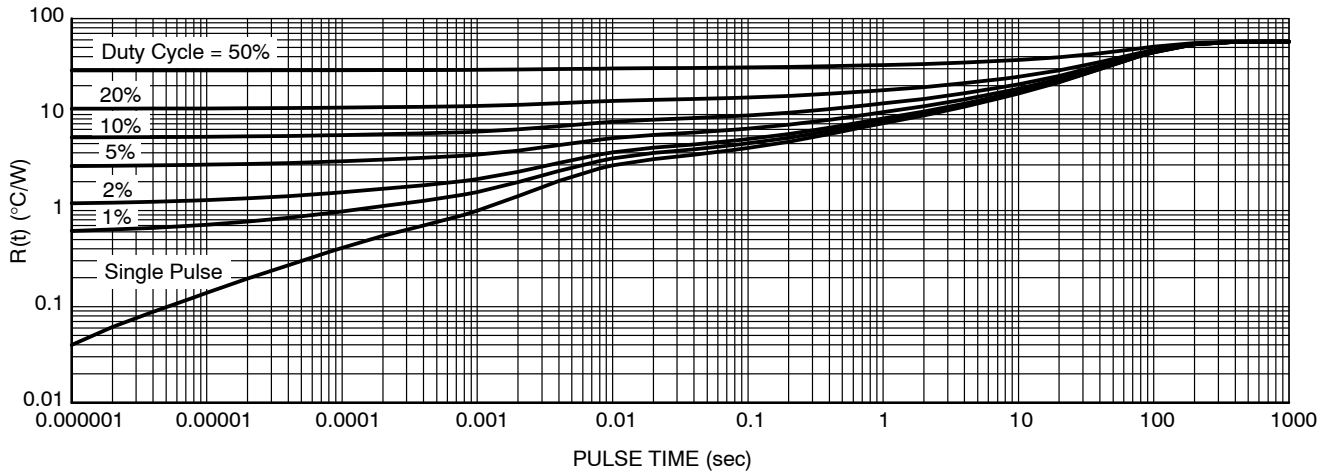


Figure 13. Thermal Response

ORDERING INFORMATION

Order Number	Package	Shipping [†]
NVD5C464NLT4G	DPAK (Pb-Free)	2500 / Tape & Reel

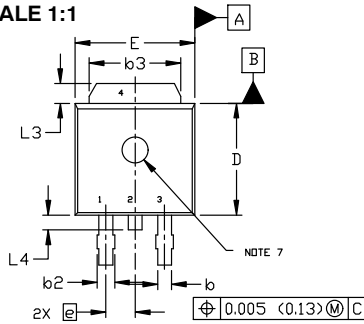
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



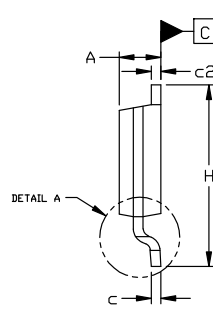
DPAK (SINGLE GAUGE)
CASE 369C
ISSUE G

DATE 31 MAY 2023

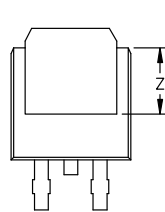
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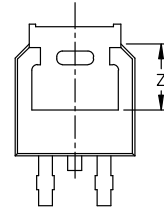
TOP VIEW



SIDE VIEW

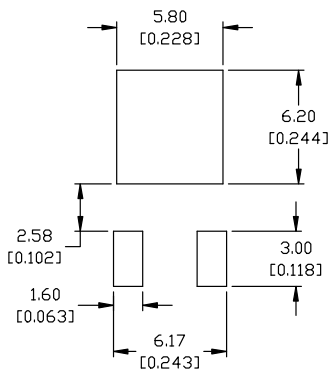


BOTTOM VIEW



BOTTOM VIEW

ALTERNATE CONSTRUCTIONS



RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

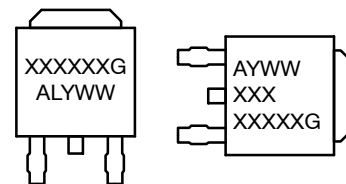
- STYLE 1: PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR
- STYLE 2: PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN
- STYLE 3: PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE
- STYLE 4: PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE
- STYLE 5: PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE
- STYLE 6: PIN 1. MT1
2. MT2
3. GATE
4. MT2
- STYLE 7: PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR
- STYLE 8: PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE
- STYLE 9: PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE
- STYLE 10: PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

NOTES:

1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	----	0.040	---	1.01
Z	0.155	----	3.93	---

GENERIC MARKING DIAGRAM*



- IC
- Discrete
- XXXXXX = Device Code
- A = Assembly Location
- L = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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